

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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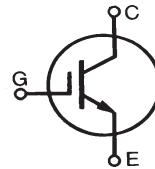
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

HiPerFAST™ IGBT

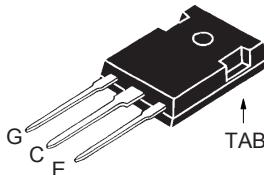
Short Circuit SOA Capability

IXSH24N60
IXSH24N60A

V_{CES}	I_{C90}	$V_{CE(sat)}$
600V	24A	2.2V
600V	24A	2.7V



TO-247 (IXSH)



G = Gate C = Collector
E = Emitter TAB = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	600	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	48	A
I_{C90}	$T_C = 90^\circ C$	24	A
I_{CM}	$T_C = 25^\circ C$, 1ms	96	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_J = 125^\circ C$, $R_G = 10\Omega$ Clamped inductive load	$I_{CM} = 48$ @ $0.8 \cdot V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V$, $V_{CE} = 360V$, $T_J = 125^\circ C$ $R_G = 82\Omega$, non repetitive	10	μs
P_c	$T_C = 25^\circ C$	150	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
M_d	Mounting torque	1.13 / 10	Nm/lb.in.
T_L	Maximum lead temperature for soldering	300	$^\circ C$
T_{SOLD}	1.6mm (0.062 in.) from case for 10s	260	$^\circ C$
Weight		6	g

Symbol	Test Conditions ($T_J = 25^\circ C$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	600		V
$V_{GE(th)}$	$I_C = 1.5mA$, $V_{CE} = V_{GE}$	4.0		V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0V$		200	μA
			1	mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$		± 100	nA
$V_{CE(sat)}$	$I_C = 24A$, $V_{GE} = 15V$, Note 1	IXSH24N60 IXSH24N60A	2.2 2.7	V

Features

- International standard package JEDEC TO-247AD
- High frequency IGBT with guaranteed Short Circuit SOA Capability
- 2nd generation HDMOS™ process
- Low $V_{CE(SAT)}$
 - for low on-state conduction losses
- MOS Gate turn-on
 - drive simplicity

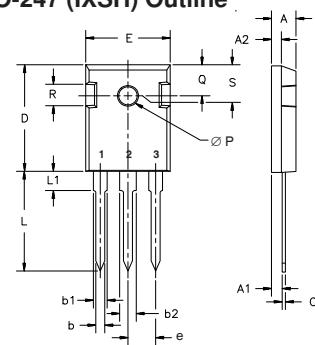
Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies
- Welding

Advantages

- Easy to mount with 1 screw (isolated mounting screw hole)
- Switching speed for high frequency applications
- High power density

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 24\text{A}$, $V_{CE} = 10\text{V}$, Note 1	9	23	S
$I_{C(ON)}$	$V_{GE} = 15\text{V}$, $V_{CE} = 10\text{V}$		65	A
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$	1800	pF	
C_{oes}		160		
C_{res}		45		
Q_g	$I_C = 24\text{A}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$	75	90	nC
Q_{ge}		20	30	nC
Q_{gc}		35	50	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 24\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 480\text{V}$, $R_G = 10\Omega$	100	ns	
t_{ri}		200		
$t_{d(off)}$		450		
t_{fi}		IXSH24N60		
E_{off}		500		
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 24\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 480\text{V}$, $R_G = 10\Omega$	275	ns	
t_{ri}		IXSH24N60A		
E_{on}		2.0		mJ
$t_{d(off)}$		IXSH24N60A		
t_{fi}		IXSH24N60A		
E_{off}		4.0	mJ	
		IXSH24N60A		mJ
R_{thJC}			0.83	$^\circ\text{C}/\text{W}$
R_{thCK}		0.21		$^\circ\text{C}/\text{W}$

TO-247 (IXSH) Outline

 Terminals: 1 - Gate
 2 - Drain
 3 - Source

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

 Notes: 1. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537